

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

DECLARATION FOR PATENT APPLICATION

COPY

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am an original, first and joint inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled:

FULLY-DEPLETED (FD) SOI MOSFET ACCESS TRANSISTOR AND METHOD OF FABRICATION

the specification of which is attached hereto.

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by an amendment, if any, specifically referred to in this oath or declaration.

I acknowledge the duty to disclose all information known to me which is material to patentability as defined in Title 37, Code of Federal Regulations, § 1.56.

I hereby claim foreign priority benefits under Title 35, United States Code § 119/365 of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

Prior Foreign Application(s)	Priority Not Claimed		
(Number) _____	(Country) _____	(Filing Date) _____	<input type="checkbox"/>
(Number) _____	(Country) _____	(Filing Date) _____	<input type="checkbox"/>
(Number) _____	(Country) _____	(Filing Date) _____	<input type="checkbox"/>

I hereby claim the benefit under Title 35, United States Code, § 120/365 of any United States and PCT international application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior

United States application in the manner provided by the first paragraph of Title 35, United States Code, § 112, I acknowledge the duty to disclose all information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations, § 1.56(a) which became available between the filing date of the prior application and the national or PCT international filing date of this application:

(Application No.)	(Filing Date)	(Status) (patented, pending, abandoned)
(Application No.)	(Filing Date)	(Status) (patented, pending, abandoned)
(Application No.)	(Filing Date)	(Status) (patented, pending, abandoned)

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Please address all correspondence to Thomas J. D'Amico of Dickstein Shapiro Morin & Oshinsky LLP located at 2101 L Street NW, Washington, DC 20037-1526. Telephone calls should be made to (202) 785-9700.

Full name of first inventor: Hongmei Wang

Inventor's signature: Hongmei Wang Date: 05/23/02

Residence: Boise, Idaho

Citizenship:

Mailing Address: 1656 S. Loggers Pond Pl.
Apt. 34
Boise, Idaho 83706

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Signature Page for Second Inventor

Full name of second inventor: John K. Zahurak

Inventor's signature: John K. Zahurak Date: 5/23/02

Residence: Boise, Idaho

Citizenship: US

Mailing Address: 3757 Gekeler Lane #195 4337 S. Pinerest Way
Boise, Idaho 83706 Boise ID 83716

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Hongmei Wang, et al.

COPY

Application No.: Not Yet Assigned

Group Art Unit: N/A

Filed:

Examiner: Not Yet Assigned

For: **FULLY-DEPLETED (FD) SOI MOSFET
ACCESS TRANSISTOR AND METHOD
OF FABRICATION**

**POWER OF ATTORNEY BY ASSIGNEE AND
CERTIFICATE BY ASSIGNEE UNDER 37 CFR § 3.73(B)**

Assistant Commissioner for Patents
Washington, DC 20231

Dear Sir:

Micron Technology, Inc., Assignee of the entire right, title and interest in the above-identified application by virtue of the Assignment attached hereto (which is also being submitted concurrently for recordation), hereby appoints the attorneys and agents of the firm of Dickstein Shapiro Morin & Oshinsky LLP located at 2101 L Street NW, Washington, DC 20037-1526, listed as follows:

Gary M. Hoffman	26,411	John C. Luce	34,378	Ellen S. Tao	43,383
Thomas J. D'Amico	28,371	Peter McGee	35,947	Gary L. Veron	39,057
Donald A. Gregory	28,954	Edward A. Meilman	24,735	Steven I. Weisburd	27,409
James W. Brady, Jr.	32,115	Edwin Oh	45,319	Mialeeka C. Williams-Bibbs	48,037
Jon D. Grossman	32,699	William E. Powell, III	39,803	Jeremy A. Cubert	40,399
Mark J. Thronson	33,082	Steven Rubin	43,063	Gianni Minutoli	41,198
Eric Oliver	35,307	Michael J. Scheer	34,425	Michael Bergman	42,318
Laurence E. Fisher	37,131	Patrick T. Skacel	47,948	Salvatore P. Tamburo	45,153
Ryan H. Flax	48,141	Stephen A. Soffen	31,063	Peter A. Veysman	45,920
Richard LaCava	41,135	Christopher M. Tanner	41,518	Christopher S. Chow	46,493

and also, listed as follows:

Application No.: Not Yet Assigned

Patent No.: M4065.0536/P536

Charles B. Brantley, III	38,086	Kevin D. Martin	37,882	David J. Paul	34,692
Michael L. Lynch	30,871				

attorneys of Micron Technology, Inc. as its attorneys with full power of substitution to prosecute this application and to transact all business in the Patent and Trademark Office in connection therewith.

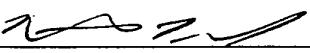
The Assignee certifies that the above-identified assignment has been reviewed and to the best of the Assignee's knowledge and belief, title is in the assignee.

Please direct all correspondence regarding this application to the following:

Thomas J. D'Amico
DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP
2101 L Street NW
Washington, DC 20037-1526
Telephone: (202) 785-9700
Fax: (202) 887-0689

Respectfully submitted,

MICRON TECHNOLOGY, INC.



Michael L. Lynch
Chief Patent Counsel
Registration No. 30,871

Dated: 6-3-02

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ASSIGNMENT AND AGREEMENT

For value received, we, Hongmei Wang and John K. Zahurak, hereby sell, assign and transfer to Micron Technology, Inc., a corporation of the State of Delaware, having an office at 8000 S. Federal Way, Boise, Idaho 83706-9632, U.S.A., and its successors, assigns and legal representatives, the entire right, title and interest, for the United States of America, in and to certain inventions related to an invention entitled FULLY-DEPLETED (FD) SOI MOSFET ACCESS TRANSISTOR AND METHOD OF FABRICATION, described in an application for Letters Patent of the United States, executed by us of even date herewith, and all the rights and privileges in said application and under any and all Letters Patent that may be granted in the United States for said inventions; and we also concurrently hereby sell, assign and transfer to Micron Technology, Inc. the entire right, title and interest in and to said inventions for all countries foreign to the United States, including all rights of priority arising from the application aforesaid, and all the rights and privileges under any and all forms of protection, including Letters Patent, that may be granted in said countries foreign to the United States for said inventions.

We authorize Micron Technology, Inc. to make application for such protection in its own name and maintain such protection in any and all countries foreign to the United States, and to invoke and claim for any application for patent or other form of protection for said inventions, without further authorization from us, any and all benefits, including the right of priority provided by any and all treaties, conventions, or agreements.

We hereby consent that a copy of this assignment shall be deemed a full legal and formal equivalent of any document which may be required in any country in proof of the right of Micron Technology, Inc. to apply for patent or other form of protection for said inventions and to claim the aforesaid benefit of the right of priority.

We request that any and all patents for said inventions be issued to Micron Technology, Inc. in the United States and in all countries foreign to the United States, or to such nominees as Micron Technology, Inc. may designate.

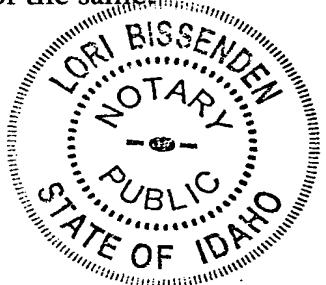
We agree that, when requested, we shall, without charge to Micron Technology, Inc. but at its expense, sign all papers, and do all acts which may be necessary, desirable or convenient in connection with said applications, patents, or other forms of protection.

Hongmei Wang
Hongmei Wang

Date: 05/23/02

United States of America)
State of Idaho) ss.:
County of Ada)

On this 23rd day of May, 2002, before me personally came Hongmei Wang, to me known to be the individual described in and who executed the foregoing instrument, and acknowledged execution of the same.



Lori Bissenden
Notary Public

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ASSIGNMENT AND AGREEMENT

Signature Page for Second Inventor

John K. Zahurak
John K. Zahurak

Date: 5/23/02

United States of America)
State of Idaho) ss.:
County of Ada)

On this 23rd day of May, 2002, before me personally came John K. Zahurak, to me known to be the individual described in and who executed the foregoing instrument, and acknowledged execution of the same.



Lori Bissenden
Notary Public